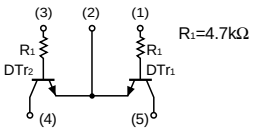
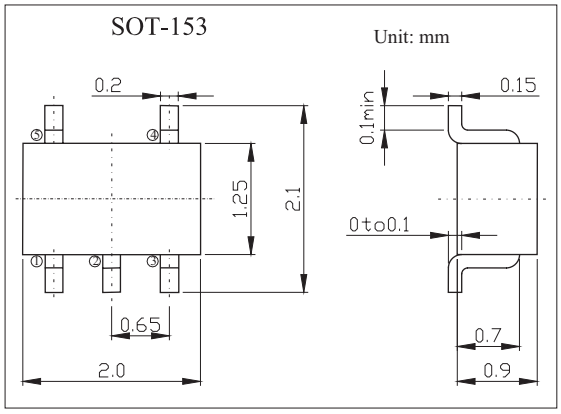
Emitter common (Dual Digital Transistors)
FMG3A

■ Features

- Dual NPN digital transistor





■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Power dissipation(Total)	P_d	300	mW
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 50 μA, I_E = 0	50			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 1 mA, I_B = 0	50			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_C = 50 μA, I_C = 0	5			V
Collector cutoff current	I_{CBO}	V_{CB}=50V, I_E=0			0.5	μA
Emitter cutoff current	I_{EBO}	V_{EB}= 4V, I_C=0			0.5	μA
DC current gain	h_{FE}	V_{CE}=5V, I_C=1mA	100	250	600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 5 mA; I_B = 0.25 mA			0.3	V
Transition frequency	f_T	V_{CE}=10V, I_E= -5m A , f=100MHz		250		MHz
Input resistance	R_1		3.29	4.7	6.11	kΩ

■ Marking

Marking	G3

FMG3A

■ Typical Characteristics

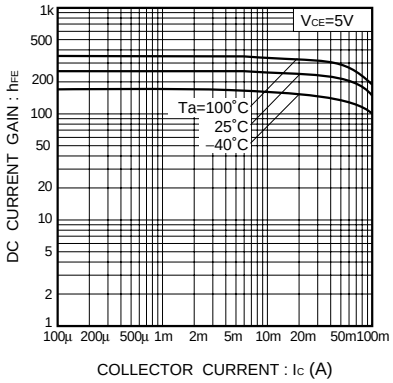


Fig.1 DC current gain vs. collector current

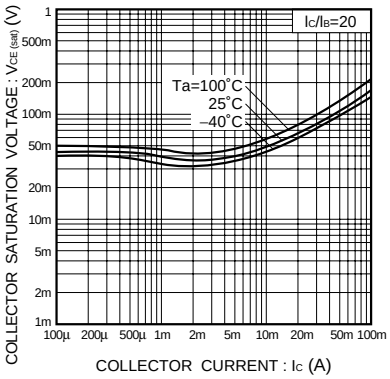


Fig.2 Collector-emitter saturation voltage vs. collector current